

EXPRESS MAIL LABEL NO.: EV343427443US

ABSTRACT OF THE DISCLOSURE

PROCESS FOR CONTACT OPENING DEFINITION
FOR ACTIVE ELEMENT ELECTRICAL CONNECTIONS

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A method is provided for contact opening definition for active element electrical connections. According to the method, a layer of BPSG is formed on a surface of an integrated circuit, and a transparent layer of nitride UV is formed above the layer of BPSG. Preferably, the transparent layer of nitride UV is formed by deposition using an HDP process and has a thickness of less than about 500Å. In one embodiment, after forming a transparent layer of nitride UV, two overlapped layers of BARC and resist are formed on the surface of the integrated circuit. Also provided is a machine-readable medium encoded with a program for contact opening definition for active element electrical connections.

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